

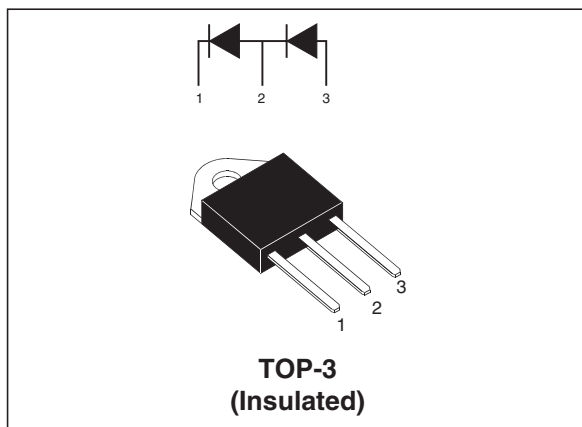
Tandem 600V HYPERFAST RECTIFIER

MAJOR PRODUCTS CHARACTERISTICS

$I_F(AV)$	30 A
V_{RRM}	600 V (in series)
$T_j(max)$	150 °C
$V_F(max)$	2.6 V
$I_{RM}(typ.)$	6.7 A

FEATURES AND BENEFITS

- ESPECIALLY SUITED AS BOOST DIODE IN CONTINUOUS MODE POWER FACTOR CORRECTORS AND HARD SWITCHING CONDITIONS
- DESIGNED FOR HIGH di_F/dt OPERATION. HYPERFAST RECOVERY CURRENT TO COMPETE WITH SiC DEVICES. ALLOWS DOWNSIZING OF MOSFET AND HEATSINKS
- INTERNAL CERAMIC INSULATED DEVICES WITH EQUAL THERMAL CONDITIONS FOR BOTH 300V DIODES
- INSULATION (2500V_{RMS}) ALLOWS PLACEMENT ON SAME HEATSINK AS MOSFET FLEXIBLE HEATSINKING ON COMMON OR SEPARATE HEATSINK.
- MATCHED DIODES FOR TYPICAL PFC APPLICATION WITHOUT NEED FOR VOLTAGE BALANCE NETWORK
- Package Capacitance: C=16pF



DESCRIPTION

The TURBOSWITCH "H" is an ultra high performance diode composed of two 300V dice in series. TURBOSWITCH "H" family drastically cuts losses in the associated MOSFET when run at high di_F/dt .

ABSOLUTE RATINGS (limiting values, for both diodes)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive peak reverse voltage		600	V
$I_F(RMS)$	RMS forward current		32	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10\text{ ms}$ sinusoidal	180	A
T_{stg}	Storage temperature range		-65 +150	°C
T_j	Maximum operating junction temperature		+ 150	°C

THERMAL AND POWER DATA

Symbol	Parameter	Test conditions	Value	Unit
$R_{th(j-c)}$	Junction to case thermal resistance	Total	1.3	°C/W
P	Conduction power dissipation for both diodes	$I_{F(AV)} = 30\text{ A}$ $\delta = 0.5$ $T_c = 20^\circ\text{C}$	100	W

STATIC ELECTRICAL CHARACTERISTICS (for both diodes)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$V_R = V_{RRM}$	$T_j = 25^\circ\text{C}$			40	μA
			$T_j = 125^\circ\text{C}$		60	400	
V_F^{**}	Forward voltage drop	$I_F = 30\text{ A}$	$T_j = 25^\circ\text{C}$			3.6	V
			$T_j = 125^\circ\text{C}$		2.1	2.6	

Pulse test : * $t_p = 100\text{ ms}$, $\delta < 2\%$

** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 1.8 \times I_{F(AV)} + 0.026 I_F^2(RMS)$$

DYNAMIC CHARACTERISTICS (for both diodes)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$I_F = 0.5\text{ A}$ $I_{rr} = 0.25\text{ A}$ $I_R = 1\text{ A}$	$T_j = 25^\circ\text{C}$		25		ns
		$I_F = 1\text{ A}$ $dI_F/dt = -50\text{ A}/\mu\text{s}$ $V_R = 30\text{ V}$				45	
I_{RM}	Reverse recovery current	$V_R = 400\text{ V}$ $I_F = 30\text{ A}$ $dI_F/dt = -200\text{ A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		6.7	8.5	A
S	Reverse recovery softness factor				0.3		-

TURN-ON SWITCHING CHARACTERISTICS (for both diodes)

Symbol	Parameter	Tests Conditions		Min.	Typ.	Max.	Unit
t_{fr}	Forward recovery time	$I_F = 30\text{ A}$ $dI_F/dt = 100\text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_F \text{ max}$	$T_j = 25^\circ\text{C}$			400	ns
V_{FP}	Transient peak forward recovery voltage	$I_F = 30\text{ A}$ $dI_F/dt = 100\text{ A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$			6	V

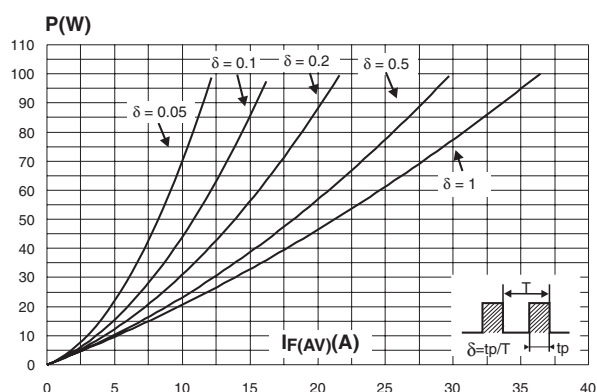
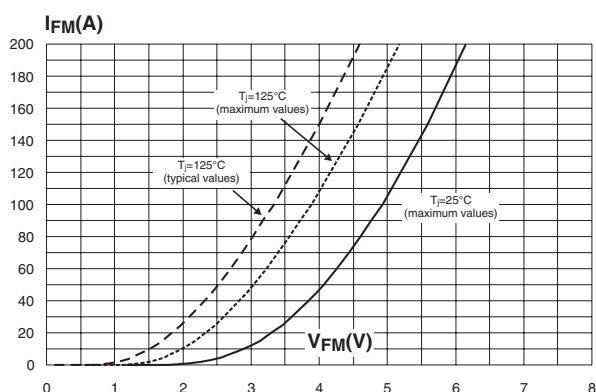
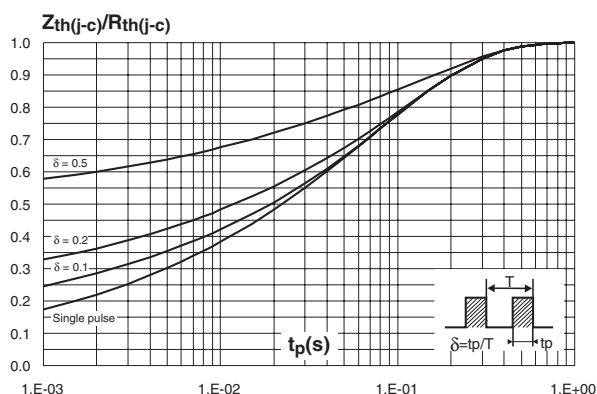
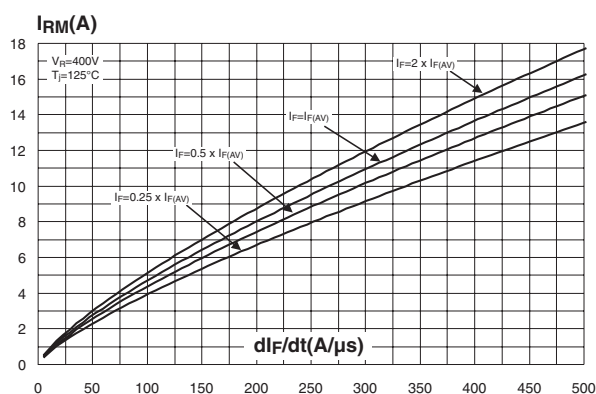
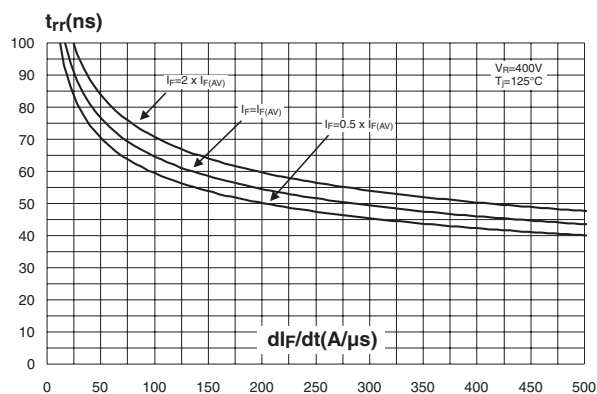
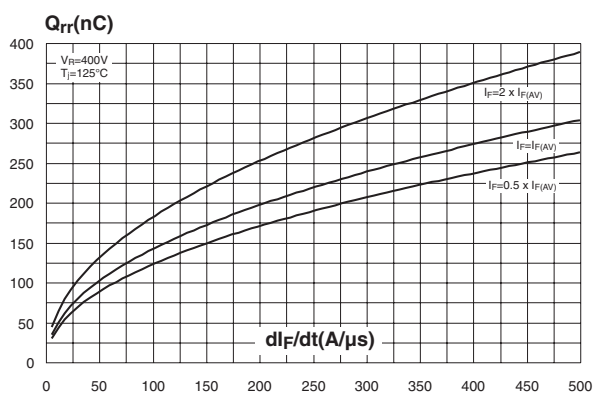
Fig. 1: Conduction losses versus average current.**Fig. 2:** Forward voltage drop versus forward current.**Fig. 3:** Relative variation of thermal impedance junction to case versus pulse duration.**Fig. 4:** Peak reverse recovery current versus di_F/dt (90% confidence).**Fig. 5:** Reverse recovery time versus di_F/dt (90% confidence).**Fig. 6:** Reverse recovery charges versus di_F/dt (90% confidence).

Fig. 7: Reverse recovery softness factor versus dl_F/dt (typical values).

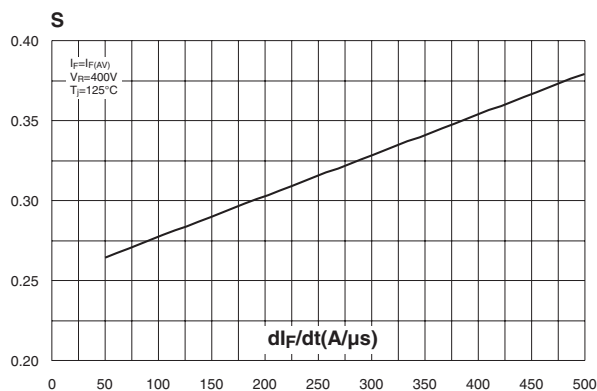


Fig. 8: Relative variation of dynamic parameters versus junction temperature (reference: $T_J = 125^\circ C$).

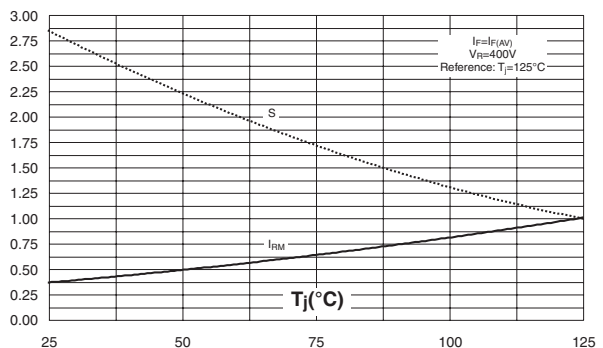


Fig. 9: Transient peak forward voltage versus dl_F/dt (90% confidence).

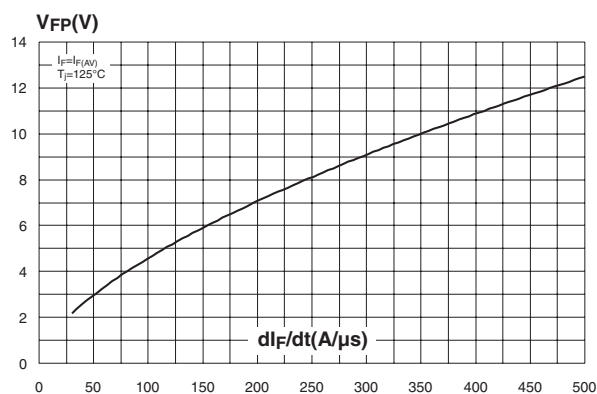


Fig. 10: Forward recovery time versus dl_F/dt (90% confidence).

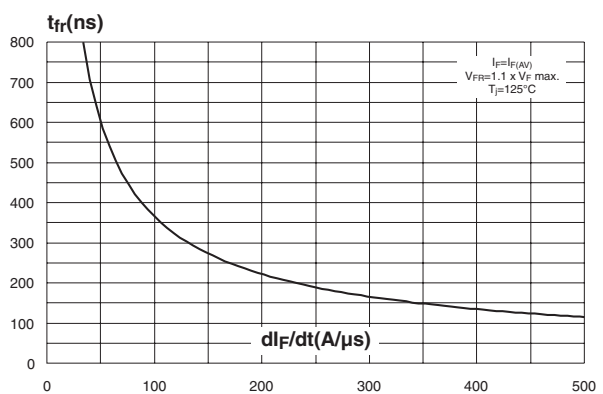
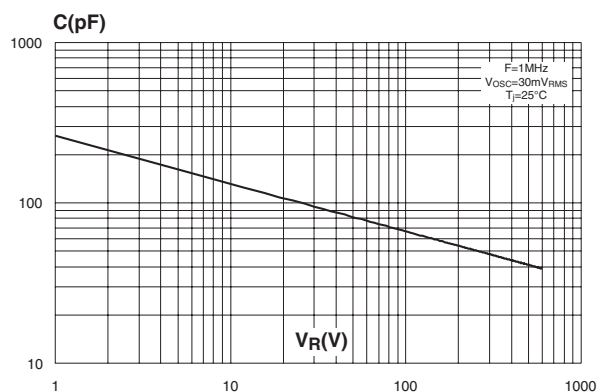


Fig. 11: Junction capacitance versus reverse voltage applied (typical values).



PACKAGE MECHANICAL DATA

TOP-3 Insulated

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.4		4.6	0.173		0.181
B	1.45		1.55	0.057		0.061
C	14.35		15.60	0.565		0.614
D	0.5		0.7	0.020		0.028
E	2.7		2.9	0.106		0.114
F	15.8		16.5	0.622		0.650
G	20.4		21.1	0.815		0.831
H	15.1		15.5	0.594		0.610
J	5.4		5.65	0.213		0.222
K	3.4		3.65	0.134		0.144
L	4.08		4.17	0.161		0.164

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH3006TPI	STTH3006TPI	TOP-3 Ins.	4.5 g.	30	Tube

- Cooling method: C
- Recommended torque value: 0.8 N.m.
- Maximum torque value: 1 N.m.
- Epoxy meets UL94,V0

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